

# **Notice of References Cited**

Application/Control No.

10/071,456

Applicant(s)/Patent Under  
Reexamination  
DICKERSON ET AL.

Examiner

Anh D. Mai

Art Unit

2814

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## **U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name		Classification
	A	US-				
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## **FOREIGN PATENT DOCUMENTS**

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## **NON-PATENT DOCUMENTS**

Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)

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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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PTO-892 (Rev. 01-2001)

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Part of Paper No. 17